

AUG 26 2002



FORM PTO-1449 <u>FIRST SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT</u>	ATTY. DOCKET NO. 1875.0220000	APPLICATION NO. 09/739,752
	APPLICANT: CHEN et al.	
	FILING DATE: December 20, 2000	GROUP: 2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE
	AA1	/		/	/		/
	AB1	/		/	/		/
P	AC1	5,163,180	11/1992	Eltoukhy et al.			
P	AD1	5,949,712	09/1999	Rao et al.			
P	AE1	5,742,555	04/1998	Marr et al.			
	AF1	6,044,012	03/2000	Rao et al. <i>Previously cited in Paper No.5</i>			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION
	AG1	/		/	/		Yes No
	AH1	/		/	/		Yes No
	AI1	/		/	/		Yes No

OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

	AJ	1	/
P	AK	1	Shi, Y., et al. "Polarity-Dependent Tunneling Current and Oxide Breakdown in Dual-Gate CMOSFET's", <i>IEEE Electron Device Letters</i> 19:391-393, (October 1998)
P	AL	1	International Search Report for PCT/US01/48853, issued by the EPO on July 31, 2002.
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/			/

EXAMINER	DATE CONSIDERED 6/18/03
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.